TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

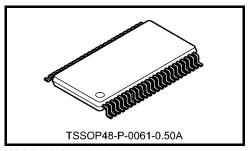
# TC74LCX164245FT

#### 16-Bit Dual Supply Bus Transceiver

The TC74LCX164245FT is a dual supply, advanced high-speed CMOS 16-bit dual supply voltage interface bus transceiver fabricated with silicon gate CMOS technology.

Designed for use as an interface between a 5-V bus and a 3.3-V or 2.5-V bus in mixed 5-V/3.3-V or 2.5-V supply systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is intended for 2 way asynchronous communication between data busses. The direction of data transmission is determined by the level of the DIR input. The enable input ( $\overline{\text{OE}}$ ) can be used to disable the device so that the buses are effectively isolated. The B-port interfaces with the 5-V bus, the A-port with the 3.3-V or 2.5-V bus.



Weight: 0.25 g (typ.)

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

#### Features (Note)

- Bidirectional interface between 5-V and 3.3-V or 2.5-V buses
- High-speed: tpd = 5.8 ns (max)

 $(V_{CCB} = 5.0 \pm 0.5 \text{ V/V}_{CCA} = 3.3 \pm 0.3 \text{ V}, \text{ Ta} = -40 \text{ to } 85^{\circ}\text{C})$ 

- Low power dissipation:  $I_{CC} = 80 \mu A \text{ (max)}$  (Ta = -40 to 85°C)
- Symmetrical ouput impedance: I<sub>OUTA</sub> = ±24 mA (min)

 $I_{OUTB} = \pm 24 \text{ mA (min)}$ 

 $(V_{CCA} = 3.0 \text{ V/V}_{CCB} = 4.5 \text{ V})$ 

- Power-down protection provided on all inputs and outputs
- Allows A port and V<sub>CCA</sub> to float simultaneously when OE is "H".
- Latch-up performance: -500 mA
- Package: TSSOP

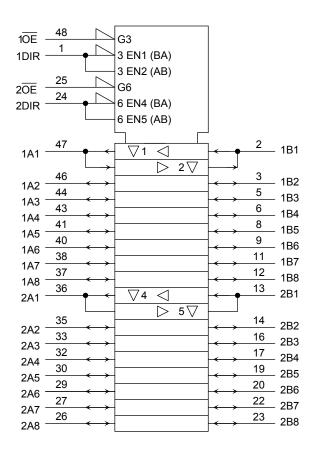
Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input fixed by means of pull-up or pull-down resistors.

#### Pin Assignment (top view)

#### 1DIR 48 10E 1B1 2 47 1A1 1B2 3 1A2 46 GND **GND** 45 1B3 5 1A3 1B4 6 43 1A4 (5 V) V<sub>CCB</sub> 42 V<sub>CCA</sub> (3.3 V) 1B5 1A5 8 1B6 9 40 1A6 GND 10 **GND** 39 1B7 11 38 1A7 1B8 12 37 1A8 2B1 13 36 2A1 2B2 14 35 2A2 GND 15 GND 34 2B3 16 33 2A3 2B4 17 32 2A4 (5 V) V<sub>CCB</sub> 18 V<sub>CCA</sub> (3.3 V) 31 2B5 19 30 2A5 2B6 20 29 2A6 GND 21 **GND** 2B7 22 27 2A7 2B8 23 26 2A8 2DIR 24 2OE 25

# **IEC Logic Symbol**



# **Truth Table**

Inp	Inputs		ction			
1OE	1DIR	Bus Bus 1A1-1A8 1B1-1B8		Outputs		
L	L	Output	Input	A = B		
L	Н	Input	Output	B=A		
Н	Х	2	Z			

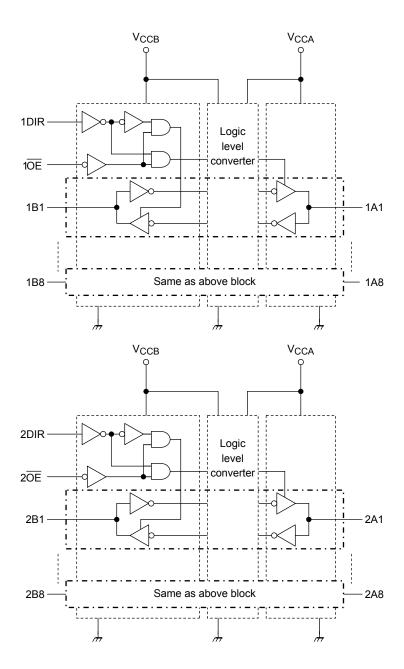
Inp	uts	Fun	ction	
2 <del>OE</del>	2DIR	Bus 2A1-2A8	Bus 2B1-2B8	Outputs
L	L	Output Input		A = B
L	Н	Input Output		B=A
Н	Х	Ž	Z	

X: Don't care

Z: High impedance

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# **Block Diagram**





#### **Absolute Maximum Ratings (Note 1)**

Characteristics	Symbol	Rating	Unit	
Power supply voltage (Note 2)	$V_{CCB}$	–0.5 to 7.0	V	
Power supply voltage (Note 2)	V <sub>CCA</sub>	-0.5 to V <sub>CCB</sub> + 0.5	v	
DC input voltage (DIR, $\overline{\text{OE}}$ )	V <sub>IN</sub>	-0.5 to 7.0	V	
		-0.5 to 7.0 (Note 3)		
	V <sub>I/OB</sub>	-0.5 to V <sub>CCB</sub> + 0.5	V	
DC bus I/O voltage		(Note 4)		
De bus 1/O voltage		-0.5 to 7.0 (Note 3)		
	V <sub>I/OA</sub>	-0.5 to V <sub>CCA</sub> + 0.5		
		(Note 4)		
Input diode current	Ι <sub>ΙΚ</sub>	-50	mA	
Output diode current	I <sub>I/OK</sub>	±50 (Note 5)	mA	
DC output ourrent	I <sub>OUTB</sub>	±50	m۸	
DC output current	I <sub>OUTA</sub>	±50	mA	
DC V <sub>CC</sub> /ground current per supply pin	I <sub>CCB</sub>	±100	mA	
DO v.Co/ground current per supply pin	I <sub>CCA</sub>	±100	IIIA	
Power dissipation	P <sub>D</sub>	400	mW	
Storage temperature	T <sub>stg</sub>	-65 to 150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

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Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2:  $V_{CCB} > V_{CCA}$ Don't supply a voltage to  $V_{CCA}$  terminal when  $V_{CCB}$  is in the off-state.

Note 3: OFF state

Note 4: High or low state. IOUT absolute maximum rating must be observed.

Note 5:  $V_{OUT} < GND$ ,  $V_{OUT} > V_{CC}$ 



# **Operating Ranges (Note 1)**

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V <sub>CCB</sub>	4.5 to 5.5	V	
Tower supply voltage	V <sub>CCA</sub>	2.3 to 3.6	V	
Input voltage (DIR, $\overline{OE}$ )	V <sub>IN</sub>	0 to 5.5	٧	
	Vyon	0 to 5.5 (Note 2)		
Bus I/O voltage	V <sub>I/OB</sub>	0 to V <sub>CCB</sub> (Note 3)	V	
Bus I/O voitage	Viva	0 to 5.5 (Note 2)	V	
	V <sub>I/OA</sub>	0 to V <sub>CCA</sub> (Note 3)		
	la	±24 (Note 4)		
Output current	Іоитв	±24 (Note 5)	mA	
	I <sub>OUTA</sub>	±8 (Note 6)		
Operating temperature	T <sub>opr</sub>	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 7)	ns/V	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND. Please connect both bus inputs and the bus outputs with VCC or GND when the I/O of the bus terminal changes by the function. In this case, please note that the output is not short-circuited.

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- Note 2: OFF state
- Note 3: High or low state
- Note 4:  $V_{CCB} = 4.5 \text{ to } 5.5 \text{ V}$
- Note 5:  $V_{CCA} = 3.0 \text{ to } 3.6 \text{ V}$
- Note 6:  $V_{CCA} = 2.3 \text{ to } 2.7 \text{ V}$
- Note 7:  $V_{INB} = 0.8$  to 2.0 V,  $V_{CCB} = 5.0$  V
  - $V_{\mbox{\footnotesize{INA}}} = 0.8$  to 2.0 V,  $V_{\mbox{\footnotesize{CCA}}} = 3.0$  V



# **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol	Test Condition		V <sub>CCB</sub> (V)	V <sub>CCA</sub> (V)		Ta = -40 to 85°C	
						Min	Max	
	V <sub>IHB</sub>	DIR, OE, Bn		$5.0 \pm 0.5$	2.3 to 3.6	2.0	_	
H-level input voltage	V	Δ		5.0 ± 0.5	$2.5\pm0.2$	1.7	_	٧
	V <sub>IHA</sub>	All	An		$3.3 \pm 0.3$	2.0	_	
	V <sub>ILB</sub>	DIR, $\overline{\text{OE}}$ , Bn		$5.0\pm0.5$	2.3 to 3.6	_	0.8	
L-level input voltage	V	An		$5.0\pm0.5$	$2.5\pm0.2$	_	0.7	V
	V <sub>ILA</sub>	All		5.0 ± 0.5	$3.3 \pm 0.3$	_	0.8	
	V <sub>OHB</sub>		I <sub>OHB</sub> = -100 μA	5.0 ± 0.5	2.3 to 3.6	V <sub>CCB</sub> - 0.2	_	
		V <sub>INA</sub> = V <sub>IHA</sub> or V <sub>ILA</sub>	I <sub>OHB</sub> = -24 mA	4.5	2.3 to 3.6	3.7	_	
H-level output voltage		VINB = VIHB or VILB	I <sub>OHA</sub> = -100 μA	5.0 ± 0.5	2.3 to 3.6	V <sub>CCA</sub> - 0.2	_	V
	V <sub>OHA</sub>	- AIHR OL AITR	I <sub>OHA</sub> = -24 mA	5.0 ± 0.5	3.0	2.2	_	
			$I_{OHA} = -8 \text{ mA}$	5.0 ± 0.5	2.3	1.8	_	
	V <sub>OLB</sub>	VINA = VIHA OR VILA VINB = VIHB OR VILB	I <sub>OLB</sub> = 100 μA	$5.0\pm0.5$	2.3 to 3.6	_	0.2	V
			I <sub>OLB</sub> = 24 mA	4.5	2.3 to 3.6	_	0.44	
L-level output voltage	Vola		I <sub>OLA</sub> = 100 μA	5.0 ± 0.5	2.3 to 3.6	_	0.2	
			I <sub>OLA</sub> = 24 mA	5.0 ± 0.5	3.0	_	0.55	
			I <sub>OLA</sub> = 8 mA	5.0 ± 0.5	2.3	_	0.6	
	I <sub>OZB</sub>	$V_{IN} = V_{IHB}$ or $V_{I/OB} = 0$ to 5.5		5.0 ± 0.5	2.3 to 3.6	_	±5.0	
3-state output OFF state current	loza	$V_{IN} = V_{IHB}$ or $V_{I/OA} = 0$ to 5.5	5.0 ± 0.5	2.3 to 3.6	_	±5.0	μА	
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> (DIR, $\overline{\text{OE}}$ )	= 0 to 5.5 V	5.5	3.6	_	±5.0	μА
Power-off leakage current	loff	V <sub>INA</sub> /V <sub>INB</sub> = 5.5	5 V	0	0	_	10	μА
	I <sub>CCB1</sub>	$V_{I/OA}$ = Open, $V_{CCA}$ = Open $V_{INB}$ = $V_{CCB}$ or GND $\overline{OE}$ = $V_{CCB}$ , DIR = GND		5.5	Open	_	80	
Quiescent supply current	I <sub>CCB2</sub>	V <sub>INA</sub> = V <sub>CCA</sub> or GND V <sub>INB</sub> = V <sub>CCB</sub> or GND		5.5	3.6	_	80	μА
	ICCA	$V_{INA} = V_{CCA}$ or $V_{INB} = V_{CCB}$ or		5.5	3.6	_	50	
	Ісств	V <sub>INB</sub> = 3.4 V pe	r input	5.5	2.3 to 3.6	_	2.0	mA
	ICCTA	V <sub>INA</sub> = V <sub>CCA</sub> -	0.6 V per input	5.0 ± 0.5	3.6	_	500	μА

# AC Characteristics (input: $t_r = t_f = 2.5 \text{ ns}$ , $R_L = 500 \Omega$ )

 $V_{\text{CCA}} = 3.3 \pm 0.3 \; \text{V}$ 

Characteristics	Symbol	Test Condition	CL (pF)	V <sub>CCB</sub> (V)	Ta = -40 to 85°C		Unit	
					Min	Max		
Propagation delay time $(Bn \to An) \label{eq:Bn}$	t <sub>pLH</sub>	Land Da	50	5.0 ± 0.5	1.0	5.8		
3-state output enable time $(\overline{OE} \to An)$	t <sub>pZL</sub>	Input: Bn Output: An (DIR = "L")	50	5.0 ± 0.5	1.0	9.0	ns	
3-state output disable time $(\ \overline{OE} \ \to An)$	t <sub>pLZ</sub> t <sub>pHZ</sub>	(-ii: - )	50	5.0 ± 0.5	1.0	9.0		
Propagation delay time $(An \to Bn)$	t <sub>pLH</sub> t <sub>pHL</sub>	Input: An	50	5.0 ± 0.5	1.0	5.8		
3-state output enable time $(\ \overline{\sf OE} \ \to {\sf Bn})$	t <sub>pZL</sub> t <sub>pZH</sub>	Output: Bn (DIR = "H")	50	5.0 ± 0.5	1.0	8.9	ns	
3-state output disable time $(\ \overline{OE} \ \to Bn)$	t <sub>pLZ</sub> t <sub>pHZ</sub>	,	50	5.0 ± 0.5	1.0	9.0		
Output to output skew	t <sub>osLH</sub> t <sub>osHL</sub>	(Note)	50	5.0 ± 0.5	_	1.0	ns	

Note: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$ 

# $V_{CCA}=2.5\pm0.2\;V$

Characteristics	Symbol	Test Condition	CL (pF)	V <sub>CCB</sub> (V)	Ta = - 85	Unit		
					Min	Max		
Propagation delay time $(Bn \to An) \label{eq:Bn}$	t <sub>pLH</sub>		30	5.0 ± 0.5	1.0	8.4		
3-state output enable time $(\overline{\sf OE} \ \to {\sf An})$	t <sub>pZL</sub>	Input: Bn Output: An (DIR = "L")	30	5.0 ± 0.5	1.0	11.0	ns	
3-state output disable time $(\overline{\sf OE} \ \to {\sf An})$	t <sub>pLZ</sub>	(Univ = 1)	30	5.0 ± 0.5	1.0	10.0		
Propagation delay time $(An \to Bn)$	t <sub>pLH</sub>	January An	50	5.0 ± 0.5	1.0	9.0		
3-state output enable time $(\ \overline{\sf OE} \ \to {\sf Bn})$	t <sub>pZL</sub> Output: Bn	Input: An Output: Bn (DIR = "H")	50	5.0 ± 0.5	1.0	10.5	ns	
3-state output disable time $(\ \overline{OE} \ \to Bn)$	t <sub>pLZ</sub> t <sub>pHZ</sub>		50	5.0 ± 0.5	1.0	10.3		
Output to output skew	t <sub>osLH</sub> t <sub>osHL</sub>	(Note)	30 or 50	5.0 ± 0.5	_	1.0	ns	

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Note: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, \ t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$ 

# **Capacitive Characteristics (Ta = 25°C)**

# $V_{CCB} = 5.0 V$

Characteristics		Symbol	Symbol Test Circuit Test Condition		V <sub>CCA</sub> (V)	Тур.	Unit
Input capacitance		C <sub>IN</sub>	_	DIR, OE	2.5, 3.3	7	pF
Output capacitance		C <sub>I/O</sub>		An, Bn	2.5, 3.3	8	pF
		C <sub>PDA</sub>	_	$A \Rightarrow B (DIR = "H")$	2.5, 3.3	2	, ,,
Power dissipation capacitance				$B \Rightarrow A (DIR = "L")$	2.5, 3.3	26	
(N	lote)	C		A ⇒ B (DIR = "H")	2.5, 3.3	36	pF
		C <sub>PDB</sub>		$B \Rightarrow A (DIR = "L")$	2.5, 3.3	4	

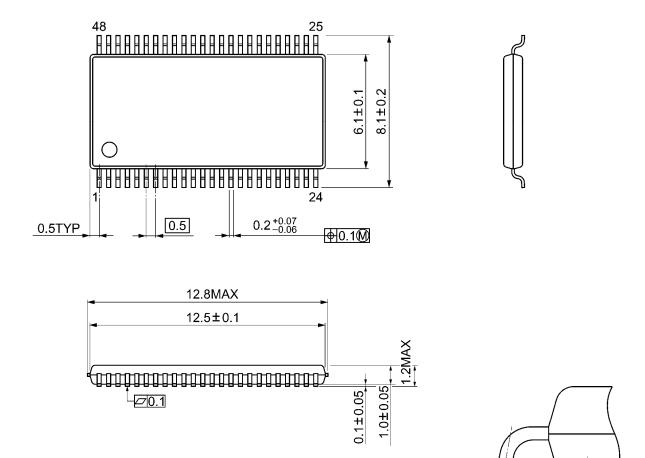
Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC \text{ (opr)}} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$ 

# **Package Dimensions**

TSSOP48-P-0061-0.50A Unit: mm



 $0.125_{-0.01}^{+0.03}$ 

(0.5)

0.45~0.75

Weight: 0.25 g (typ.)

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